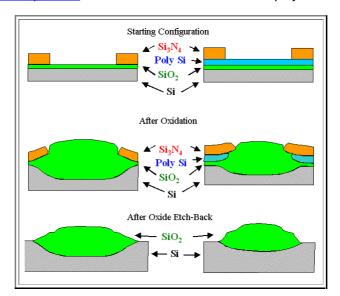
## **LOCOS** with Sacrificial Poly-Silicon

Here is a comparison of the <u>LOCOS process</u> with and without some sacrificial poly-Si:



- Provided, some of the oxide is removed by an "etch-back" process, the lateral extension can be kept somewhat smaller than in the conventional case.
- While this makes things quite complicated, the final versions of the **LOCOS** process were even more complicated.